



SHENZHEN HAOLIN ELECTRONICS TECHNOLOGY CO., LTD

DO-201AD SCHOTTKY BARRIER DIODE

Reverse Voltage -20 to 100 Volts

SR820 - SR8A0

Forward Current -8.0 Ampere

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss,high efficiency
- High current capability ,Low forward voltage drop
- Single rectifier construction
- High surge capability
- For use in low voltage ,high frequency inverters,
free wheeling , and polarity protection applications
- High temperature soldering guaranteed: 250°C/10 seconds
0.25"(6.35mm)from case

MECHANICAL DATA

- Case:** JEDEC DO-220AC molded plastic body
- Terminals:** lead solderable per MIL-STD-750,method 2026
- Polarity:** As marked
- Mounting Position:** Any
- Weight:** 0.08 ounce, 2.24 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

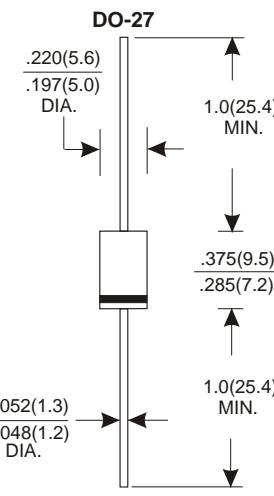
(Ratings at 25°C ambient temperature unless otherwise specified,Single phase,half wave,resistive or inductive)

load. For capacitive load,derate by 20%)

	Symbols	SR820	SR830	SR840	SR850	SR860	SR880	SR8A0	Units
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	Volts
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	57	71	Volts
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	Volts
Macimum average forward rectified current(see Fig.1)	I _(AV)						8.0		Amps
Repetitive peak forward current(square wavr, 20KHz) at T _c =105°C	I _{FRM}						16.0		Amps
Peak forward surge current 8.3ms singel half sine-wave superimposed on rated load (JEDEC method)	I _{FSM}						150.0		Amps
Maximum instantaneous forward voltage at 7.5 A(Note 1)	V _F		0.65		0.75		0.8	0.85	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	TA=25°C TA=125°C	IR			1.0				mA
			15			50			
Typeical thermal resistance(Note 2)	R _{θ_{JC}}				2.5				°C/W
Operating junction temperature range	T _J		-65 to +150			-65 to +150			°C
storage temperature range	T _{TG}				-65 to +150				°C

Notes: 1. Pulse test: 300 μ s pulse width,1% duty cycle

2.Thermal resistance from juntion to case



Dimensions in inches and (millimeters)

RATINGS AND CHARACTERISTIC CURVES SR820 THRU SR8A0(SINGLE CHIP)

FIG.1-FORWARD CURRENT DERATING CURVE

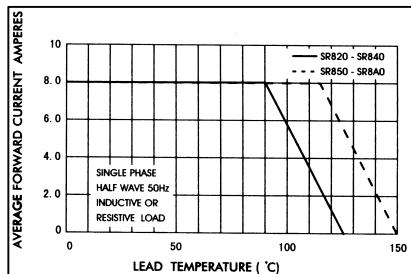


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

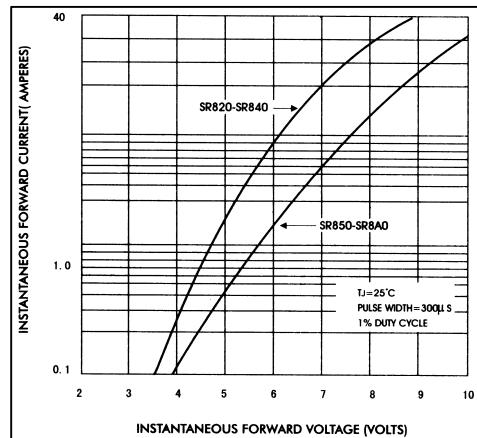


FIG.4-TYPICAL JUNCTION CAPACITANCE

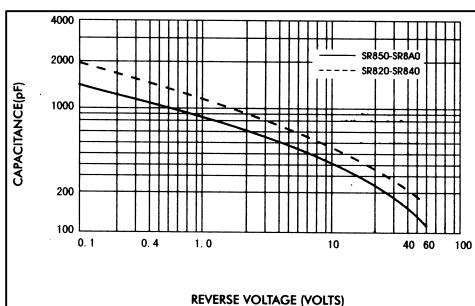


FIG.3-TYPICAL REVERSE CHARACTERISTICS

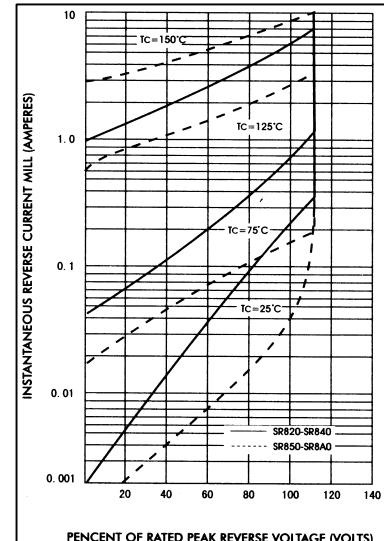


FIG.5-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

